

Philomela Komninou

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228
papers

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239
ext. papers

3,058
ext. citations

3.1
avg, IF

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L-index

#	Paper	IF	Citations
228	Direct comparison of catalyst-free and catalyst-induced GaN nanowires. <i>Nano Research</i> , 2010 , 3, 528-536	10	154
227	High-quality, large-area MoSe ₂ and MoSe ₂ /Bi ₂ Se ₃ heterostructures on AlN(0001)/Si(111) substrates by molecular beam epitaxy. <i>Nanoscale</i> , 2015 , 7, 7896-905	7.7	107
226	Properties of GaN Nanowires Grown by Molecular Beam Epitaxy. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011 , 17, 878-888	3.8	99
225	Heteroepitaxial growth of In-face InN on GaN (0001) by plasma-assisted molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2005 , 97, 113520	2.5	84
224	Synthesis, characterization and thermal properties of polymer/magnetite nanocomposites. <i>Nanotechnology</i> , 2006 , 17, 2046-2053	3.4	74
223	Axial and radial growth of Ni-induced GaN nanowires. <i>Applied Physics Letters</i> , 2007 , 91, 093113	3.4	71
222	Indium migration paths in V-defects of InAlN grown by metal-organic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2009 , 95, 071905	3.4	60
221	Internal quantum efficiency of III-nitride quantum dot superlattices grown by plasma-assisted molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2011 , 109, 103501	2.5	54
220	Misfit relaxation of the AlN/Al ₂ O ₃ (0001) interface. <i>Physical Review B</i> , 2001 , 64,	3.3	53
219	Microstructural changes of processed vitrified solid waste products. <i>Journal of the European Ceramic Society</i> , 2003 , 23, 1305-1311	6	51
218	Nanostructure and strain in InGaN/GaN superlattices grown in GaN nanowires. <i>Nanotechnology</i> , 2013 , 24, 435702	3.4	49
217	Vitrification of lead-rich solid ashes from incineration of hazardous industrial wastes. <i>Waste Management</i> , 2003 , 23, 361-71	8.6	47
216	Mechanism of compositional modulations in epitaxial InAlN films grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2009 , 95, 021913	3.4	46
215	Generation and annihilation of antiphase domain boundaries in GaAs on Si grown by molecular beam epitaxy. <i>Journal of Materials Research</i> , 1993 , 8, 1908-1921	2.5	44
214	Optical encoding by plasmon-based patterning: hard and inorganic materials become photosensitive. <i>Nano Letters</i> , 2012 , 12, 259-63	11.5	41
213	Control of the polarity of molecular-beam-epitaxy-grown GaN thin films by the surface nitridation of Al ₂ O ₃ (0001) substrates. <i>Applied Physics Letters</i> , 2002 , 80, 2886-2888	3.4	41
212	A modified empirical potential for energetic calculations of planar defects in GaN. <i>Computational Materials Science</i> , 2003 , 27, 43-49	3.2	39

211	Dislocation core investigation by geometric phase analysis and the dislocation density tensor. <i>Journal Physics D: Applied Physics</i> , 2008 , 41, 035408	3	37
210	Misfit accommodation of compact and columnar InN epilayers grown on Ga-face GaN (0001) by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2005 , 86, 151905	3.4	37
209	Defects, strain relaxation, and compositional grading in high indium content InGaN epilayers grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2015 , 118, 155301	2.5	34
208	Observation of surface Dirac cone in high-quality ultrathin epitaxial Bi ₂ Se ₃ topological insulator on AlN(0001) dielectric. <i>ACS Nano</i> , 2014 , 8, 6614-9	16.7	33
207	Structural properties of 10 ⁷ nm thick InN grown on sapphire (0001). <i>Superlattices and Microstructures</i> , 2006 , 40, 246-252	2.8	32
206	Atomic structures and energies of partial dislocations in wurtzite GaN. <i>Physical Review B</i> , 2004 , 70,	3.3	27
205	Dislocation movements and deformation twinning in zinc. <i>Acta Metallurgica</i> , 1988 , 36, 2493-2502		27
204	Optical and electrical properties of TiN/n-GaN contacts in correlation with their structural properties. <i>Semiconductor Science and Technology</i> , 2003 , 18, 594-601	1.8	26
203	Topological Analysis of Defects in Epitaxial Nitride Films and Interfaces. <i>Physica Status Solidi (B): Basic Research</i> , 2001 , 227, 45-92	1.3	26
202	Structure effects on the magnetism of AgCo nanoparticles. <i>Acta Materialia</i> , 2006 , 54, 5251-5260	8.4	24
201	Structural transition of inversion domain boundaries through interactions with stacking faults in epitaxial GaN. <i>Physical Review B</i> , 2001 , 64,	3.3	24
200	Selective-area growth of GaN nanowires on SiO ₂ -masked Si (111) substrates by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2016 , 119, 224305	2.5	24
199	Vitrification of incinerated tannery sludge in silicate matrices for chromium stabilization. <i>Waste Management</i> , 2017 , 59, 237-246	8.6	23
198	Effect of edge threading dislocations on the electronic structure of InN. <i>Applied Physics Letters</i> , 2011 , 98, 072103	3.4	22
197	Misfit dislocations and antiphase domain boundaries in GaAs/Si interface. <i>Journal of Applied Physics</i> , 1994 , 75, 143-152	2.5	22
196	Low-field giant magnetoresistance in (111)-textured Co/Au multilayers prepared with magnetron sputtering. <i>Journal of Applied Physics</i> , 1998 , 84, 6221-6228	2.5	21
195	Partial dislocations in wurtzite GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 2888-2899	1.6	21
194	Effects of the Sapphire Nitridation on the Polarity and Structural Properties of GaN Layers Grown by Plasma-Assisted MBE. <i>Physica Status Solidi A</i> , 2001 , 188, 567-570		21

193	On the deposition mechanisms and the formation of glassy Cu ₂ S thin films. <i>Journal of Applied Physics</i> , 2010 , 107, 084313	2.5	20
192	Morphology and strain of self-assembled semipolar GaN quantum dots in (112̄) AlN. <i>Journal of Applied Physics</i> , 2010 , 108, 104304	2.5	20
191	Analysis of partial dislocations in wurtzite GaN using gradient elasticity. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 2161-2166	1.6	20
190	High power ultraviolet light emitting diodes based on GaN/AlGaIn quantum wells produced by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2006 , 100, 104506	2.5	19
189	Improved luminescence and thermal stability of semipolar (11-22) InGaIn quantum dots. <i>Applied Physics Letters</i> , 2011 , 98, 201911	3.4	18
188	Structural role and coordination environment of Fe in Fe ₂ O ₃ /PbO/SiO ₂ /Na ₂ O composite glasses. <i>Journal of Non-Crystalline Solids</i> , 2008 , 354, 105-111	3.9	18
187	Effects of ion implantation on the mechanical behavior of GaN films. <i>Thin Solid Films</i> , 2007 , 515, 3011-3018	3.8	18
186	Interatomic potential calculations of III(Al, In) planar defects with a III-species environment approach. <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 1118-1124	1.3	18
185	Epitaxial growth and self-organized superlattice structures in AlGaIn films grown by plasma assisted molecular beam epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001 , 87, 227-236	3.1	18
184	Slip transfer across low-angle grain boundaries of deformed Titanium. <i>Scripta Metallurgica Et Materialia</i> , 1995 , 33, 1883-1888	3.8	18
183	Broad compositional tunability of indium tin oxide nanowires grown by the vapor-liquid-solid mechanism. <i>APL Materials</i> , 2014 , 2, 056104	5.7	17
182	Piezoelectric InAs (211)B quantum dots grown by molecular beam epitaxy: Structural and optical properties. <i>Journal of Applied Physics</i> , 2010 , 108, 103525	2.5	17
181	Polar AlN/GaN interfaces: Structures and energetics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1892-1897	1.6	17
180	Study of annealing induced devitrification of stabilized industrial waste glasses by means of micro-X-ray fluorescence mapping and absorption fine structure spectroscopy. <i>Journal of Non-Crystalline Solids</i> , 2005 , 351, 2474-2480	3.9	17
179	Understanding the effects of Si (111) nitridation on the spontaneous growth and properties of GaN nanowires. <i>Journal of Crystal Growth</i> , 2016 , 442, 8-13	1.6	16
178	Silver nanoparticles and graphitic carbon through thermal decomposition of a silver/acetylenedicarboxylic salt. <i>Nanoscale Research Letters</i> , 2009 , 4, 1358-64	5	16
177	Metal-containing amorphous carbon (a-C:Ag) and AlN (AlN:Ag) metallo-dielectric nanocomposites. <i>Thin Solid Films</i> , 2009 , 518, 1508-1511	2.2	16
176	Crystal phase separation and microstructure of a thermally treated vitrified solid waste. <i>Journal of the European Ceramic Society</i> , 2006 , 26, 1141-1148	6	16

175	Dependence of exchange bias energy on spin projections at (La,Ca)MnO ₃ ferromagnetic/antiferromagnetic interfaces. <i>Journal of Applied Physics</i> , 2002 , 92, 397-405	2.5	16
174	The Microstructure of Ti/Al and TiN Ohmic Contacts to Gallium Nitride. <i>Physica Status Solidi A</i> , 1999 , 176, 767-771		16
173	Electronic structure of 1/6<202̄B> partial dislocations in wurtzite GaN. <i>Journal of Applied Physics</i> , 2011 , 109, 083511	2.5	15
172	Structural characterization of Na ₂ O-LaO-Bi ₂ O ₃ glass ceramics reinforced with electric arc furnace dust. <i>Journal of the European Ceramic Society</i> , 2007 , 27, 2423-2431	6	15
171	On the distribution and bonding environment of Zn and Fe in glasses containing electric arc furnace dust: a mu-XAFS and mu-XRF study. <i>Journal of Hazardous Materials</i> , 2007 , 142, 297-304	12.8	15
170	Effect of composition and annealing temperature on the mechanical properties of a vitrified waste. <i>Journal of the European Ceramic Society</i> , 2004 , 24, 2095-2102	6	15
169	Gold films epitaxially grown by diffusion at the 3C-BiC/Si interface. <i>Journal of Crystal Growth</i> , 1999 , 203, 103-112	1.6	15
168	Structural anisotropic properties of a-plane GaN epilayers grown on r-plane sapphire by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2014 , 115, 213506	2.5	15
167	Transport properties of metal-semiconductor junctions on n-type InP prepared by electrophoretic deposition of Pt nanoparticles. <i>Semiconductor Science and Technology</i> , 2014 , 29, 045017	1.8	14
166	Growth of InAs/GaAs quantum dots covered by GaAsSb in multiple structures studied by reflectance anisotropy spectroscopy. <i>Journal of Crystal Growth</i> , 2015 , 414, 156-160	1.6	14
165	Stranski-Krastanow growth of (112̄2)-oriented GaN/AlN quantum dots. <i>Applied Physics Letters</i> , 2009 , 94, 111901	3.4	14
164	Step-induced misorientation of GaN grown on r-plane sapphire. <i>Applied Physics Letters</i> , 2008 , 93, 021910	3.4	14
163	Polycrystalline diamond formation by post-growth ion bombardment of sputter-deposited amorphous carbon films. <i>Carbon</i> , 1999 , 37, 865-869	10.4	14
162	Nanospheres and nanoflowers of copper bismuth sulphide (Cu ₃ BiS ₃): Colloidal synthesis, structural, optical and electrical characterization. <i>Journal of Alloys and Compounds</i> , 2019 , 776, 142-148	5.7	14
161	Screw threading dislocations in AlN: Structural and electronic properties of In and O doped material. <i>Journal of Applied Physics</i> , 2011 , 110, 053715	2.5	13
160	Atomic core configurations of the -screw basal dislocation in wurtzite GaN. <i>Journal of Crystal Growth</i> , 2007 , 300, 212-216	1.6	13
159	Study of InN/GaN interfaces using molecular dynamics. <i>Journal of Materials Science</i> , 2008 , 43, 3982-3988	4.3	13
158	Correlation between nucleation, morphology and residual strain of InN grown on Ga-face GaN (0001). <i>Journal of Crystal Growth</i> , 2005 , 278, 367-372	1.6	13

157	Growth of fcc Co in sputter-deposited Co/Au multilayers with (111) texture. <i>Journal of Crystal Growth</i> , 2000 , 208, 401-408	1.6	13
156	Core models of a-edge threading dislocations in wurtzite III(Al,Ga,In)-nitrides. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1931-1935	1.6	12
155	Interfacial structure of semipolar AlN grown on m-plane sapphire by MBE. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1637-1640	1.3	12
154	Structural and electronic properties of GaN nanowires with embedded In _x Ga _{1-x} N nanodisks. <i>Journal of Applied Physics</i> , 2015 , 118, 034301	2.5	11
153	3D modelling of misfit networks in the interface region of heterostructures. <i>Journal Physics D: Applied Physics</i> , 2007 , 40, 4084-4091	3	11
152	Strain distribution of thin InN epilayers grown on (0001) GaN templates by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2007 , 90, 061920	3.4	11
151	Microstructural assessment of InN-on-GaN films grown by plasma-assisted MBE. <i>Superlattices and Microstructures</i> , 2004 , 36, 509-515	2.8	11
150	Microstructure of planar defects and their interactions in wurtzite GaN films. <i>Solid-State Electronics</i> , 2003 , 47, 553-557	1.7	11
149	Junction Line Disclinations: Characterisation and Observations. <i>Journal of Materials Science</i> , 1999 , 7, 217-229		11
148	Effect of the lower and upper interfaces on the quality of InAs/GaAs quantum dots. <i>Applied Surface Science</i> , 2014 , 301, 173-177	6.7	10
147	Optical properties of GaN-based nanowires containing a single Al(0.14)Ga(0.86)N/GaN quantum disc. <i>Nanotechnology</i> , 2013 , 24, 125201	3.4	10
146	Junction lines of inversion domain boundaries with stacking faults in GaN. <i>Physical Review B</i> , 2004 , 70,	3.3	10
145	Ultrafast pulsed laser deposition of carbon nanostructures: Structural and optical characterization. <i>Applied Surface Science</i> , 2013 , 278, 101-105	6.7	9
144	Structural properties of SnO ₂ nanowires and the effect of donor like defects on its charge distribution. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 226-229	1.6	9
143	Dissociation of the 60° basal dislocation in wurtzite GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 84-88		9
142	The 60° basal dislocation in wurtzite GaN: Energetics, electronic and core structures. <i>Computational Materials Science</i> , 2013 , 79, 118-124	3.2	9
141	Comparison of Fe and Si doping of GaN: An EXAFS and Raman study. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2011 , 176, 723-726	3.1	9
140	Growth and characterization of polar (0001) and semipolar (11̄02) InGa _N /GaN quantum dots. <i>Journal of Crystal Growth</i> , 2011 , 323, 161-163	1.6	9

139	Strain relaxation in AlN/GaN heterostructures grown by molecular beam epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2569-2572	1.6	9
138	Energetics of the 30° Shockley partial dislocation in wurtzite GaN. <i>Superlattices and Microstructures</i> , 2006 , 40, 458-463	2.8	9
137	Interfacial structure of MBE grown InN on GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 777-780	1.6	9
136	Crystalline structures of carbon complexes in amorphous carbon films. <i>Diamond and Related Materials</i> , 2000 , 9, 703-706	3.5	9
135	Defect microstructure in laser-assisted modulation molecular-beam epitaxy GaAs on (100) silicon. <i>Journal of Applied Physics</i> , 1990 , 68, 3298-3302	2.5	9
134	Compositional and strain analysis of In(Ga)N/GaN short period superlattices. <i>Journal of Applied Physics</i> , 2018 , 123, 024304	2.5	8
133	Ordered structures in III-Nitride ternary alloys. <i>Computational Materials Science</i> , 2016 , 118, 22-31	3.2	8
132	Growth mechanism and microstructure of low defect density InN (0001) In-face thin films on Si (111) substrates. <i>Journal of Applied Physics</i> , 2013 , 114, 163519	2.5	8
131	MOVPE prepared InAs/GaAs quantum dots covered by GaAsSb layer with long wavelength emission at 1.8 μm. <i>Journal of Crystal Growth</i> , 2015 , 414, 167-171	1.6	8
130	Combined vertically correlated InAs and GaAsSb quantum dots separated by triangular GaAsSb barrier. <i>Journal of Applied Physics</i> , 2013 , 114, 174305	2.5	8
129	Electronic properties and bonding characteristics of AlN:Ag thin film nanocomposites. <i>Journal of Applied Physics</i> , 2011 , 109, 054310	2.5	8
128	Structure, stability and mechanical performance of AlN:Ag nanocomposite films. <i>Surface and Coatings Technology</i> , 2010 , 204, 1937-1941	4.4	8
127	Depth profile of the biaxial strain in a 10 th thick InN (0001) film. <i>Journal of Applied Physics</i> , 2006 , 100, 113516	2.5	8
126	Mixed partial dislocation core structure in GaN by high resolution electron microscopy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 2156-2160	1.6	8
125	Structural properties of ZnSe epilayers on (111) GaAs. <i>Journal of Applied Physics</i> , 2001 , 90, 3301-3307	2.5	8
124	A parametric study of implantation-induced variations on the mechanical properties of epitaxial GaN. <i>Journal of Physics Condensed Matter</i> , 2002 , 14, 12953-12959	1.8	8
123	Atomic-scale models of interactions between inversion domain boundaries and intrinsic basal stacking faults in GaN. <i>Diamond and Related Materials</i> , 2002 , 11, 905-909	3.5	8
122	Microstructure of GaN Films Grown by RF-Plasma Assisted Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 639, 3471		8

121	Influence of laser annealing on the structural properties of sputtered AlN:Ag plasmonic nanocomposites. <i>Journal of Materials Science</i> , 2014 , 49, 3996-4006	4.3	7
120	Misfit dislocation reduction in InGaAs epilayers grown on porous GaAs substrates. <i>Applied Surface Science</i> , 2014 , 306, 89-93	6.7	7
119	Morphology and origin of V-defects in semipolar (11 $\bar{2}$) InGaN. <i>Journal of Crystal Growth</i> , 2012 , 339, 1-7	1.6	7
118	Effect of AlN interlayers in the structure of GaN-on-Si grown by plasma-assisted MBE. <i>Journal of Crystal Growth</i> , 2009 , 311, 2010-2015	1.6	7
117	Reconstructions and electronic structure of (112 $\bar{2}$) and (112 $\bar{2}$) semipolar AlN surfaces. <i>Journal of Applied Physics</i> , 2012 , 112, 033510	2.5	7
116	Topology of twin junctions in epitaxial β -SiC. <i>Diamond and Related Materials</i> , 1997 , 6, 1362-1364	3.5	7
115	Defect characterization and analysis of III-V nanowires grown by Ni-promoted MBE. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2589-2592	1.6	7
114	Raman and transmission electron microscopy characterization of InN samples grown on GaN/Al ₂ O ₃ by molecular beam epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1588-1593	1.3	7
113	Correlation of structure and magnetism of AgCo nanoparticle arrays. <i>Journal of Magnetism and Magnetic Materials</i> , 2004 , 272-276, E1253-E1254	2.8	7
112	Interfacial and defect structures in multilayered GaN/AlN films. <i>Journal of Physics Condensed Matter</i> , 2002 , 14, 13277-13283	1.8	7
111	Anisotropic microhardness and crack propagation in epitaxially grown GaN films. <i>Journal of Physics Condensed Matter</i> , 2000 , 12, 10241-10247	1.8	7
110	Interfacial dislocation arrays in twin boundaries of deformed titanium. <i>Scripta Metallurgica Et Materialia</i> , 1994 , 30, 1311-1315		7
109	The influence of structural characteristics on the electronic and thermal properties of GaN/AlN core/shell nanowires. <i>Journal of Applied Physics</i> , 2016 , 119, 074304	2.5	7
108	Laser-matter interactions, phase changes and diffusion phenomena during laser annealing of plasmonic AlN:Ag templates and their applications in optical encoding. <i>Journal Physics D: Applied Physics</i> , 2015 , 48, 285306	3	6
107	Structural properties of semipolar InGaN/GaN quantum dot superlattices grown by plasma-assisted MBE. <i>Microelectronic Engineering</i> , 2012 , 90, 108-111	2.5	6
106	Structure and strain state of polar and semipolar InGaN quantum dots. <i>Applied Surface Science</i> , 2012 , 260, 7-12	6.7	6
105	Microstructure of N-face InN grown on Si (111) by plasma-assisted MBE using a thin GaN/AlN buffer layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1074-1078	1.6	6
104	Electron microscopy investigation of extended defects in a-plane gallium nitride layers grown on r-plane sapphire by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 3748-3751		6

103	Application of EXAFS for the determination of the crystallization ratio in a series of vitro-ceramic materials containing industrial waste. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006 , 246, 238-243	1.2	6
102	Interfacial dislocations in TiN/GaN thin films. <i>Journal of Physics Condensed Matter</i> , 2000 , 12, 10295-10300.	0.8	6
101	High-symmetry triple junctions in polycrystalline silicon. <i>Journal of Applied Crystallography</i> , 1991 , 24, 232-238	3.8	6
100	The heterogeneous nucleation of threading dislocations on partial dislocations in III-nitride epilayers. <i>Scientific Reports</i> , 2020 , 10, 17371	4.9	6
99	Strain and elastic constants of GaN and InN. <i>Computational Condensed Matter</i> , 2017 , 10, 25-30	1.7	5
98	Effects of ultrathin AlN prelayers on the spontaneous growth of GaN nanowires by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2019 , 514, 89-97	1.6	5
97	Decorated Dislocations against Phonon Propagation for Thermal Management. <i>ACS Applied Energy Materials</i> , 2020 , 3, 2682-2694	6.1	5
96	Nanostructure and strain properties of core-shell GaAs/AlGaAs nanowires. <i>Semiconductor Science and Technology</i> , 2015 , 30, 114012	1.8	5
95	Self-annihilation of inversion domains by high energy defects in III-Nitrides. <i>Applied Physics Letters</i> , 2014 , 104, 141914	3.4	5
94	Atomistic modeling and HRTEM analysis of misfit dislocations in InN/GaN heterostructures. <i>Applied Surface Science</i> , 2012 , 260, 23-28	6.7	5
93	Strain accommodation and interfacial structure of AlN interlayers in GaN. <i>Crystal Research and Technology</i> , 2009 , 44, 1170-1180	1.3	5
92	Controlled growth of porous networks in phosphide semiconductors. <i>Journal of Porous Materials</i> , 2008 , 15, 75-81	2.4	5
91	Atomic-scale configuration of catalyst particles on GaN nanowires. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 3716-3719		5
90	Effect of composition on the bonding environment of In in InAlN and InGaN epilayers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2593-2597	1.6	5
89	On the coordination environment of Fe- and Pb-rich solidified industrial waste: An X-ray absorption and Mössbauer study. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 2933-2942	3.9	5
88	InN quantum dots grown on GaN (0001) by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 3983-3987		5
87	Interfacial steps, dislocations, and inversion domain boundaries in the GaN/AlN/Si (0001)/(111) epitaxial system. <i>Physica Status Solidi (B): Basic Research</i> , 2005 , 242, 1617-1627	1.3	5
86	Disconnections at translation domain boundaries in epitaxial GaN. <i>Journal of Physics Condensed Matter</i> , 2002 , 14, 12709-12715	1.8	5

85	Energetic, structural and electronic properties of metal vacancies in strained AlN/GaN interfaces. <i>Journal of Physics Condensed Matter</i> , 2015 , 27, 125006	1.8	4
84	Deformation and fracture in (0001) and (10-10) GaN single crystals. <i>Materials Science and Technology</i> , 2018 , 34, 1531-1538	1.5	4
83	Structural and electronic properties of elastically strained InN/GaN quantum well multilayer heterostructures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 289-292		4
82	Si nanostructures grown by picosecond high repetition rate pulsed laser deposition. <i>Applied Surface Science</i> , 2013 , 278, 67-70	6.7	4
81	Structural characterization of InN epilayers grown on r-plane sapphire by plasma-assisted MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 534-537		4
80	InGaN/GaN quantum dots as optical probes for the electric field at the GaN/electrolyte interface. <i>Journal of Applied Physics</i> , 2013 , 114, 074313	2.5	4
79	Indium adsorption and incorporation mechanisms in AlN. <i>Journal of Materials Science</i> , 2011 , 46, 4377-4383	4.3	4
78	Nanocrystalline thin titanium films grown on potassium bromide single crystals. <i>Thin Solid Films</i> , 1998 , 319, 140-143	2.2	4
77	Temperature dependent EXAFS of InN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2611-2614	1.6	4
76	Structural and optical characterisation of thick InN epilayers grown with a single or two step growth process on GaN(0001). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 162-166	1.6	4
75	Modification of the Fe-environment in Fe ₂ O ₃ glass/glass ceramic systems containing Pb, Na and Si. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006 , 246, 170-175	1.2	4
74	XAFS Studies on Vitrified Industrial Waste. <i>Physica Scripta</i> , 2005 , 931	2.6	4
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